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IN THE CLAIMS

1. (currently amended) A method of processing a substrate, the method comprising the sequential steps of:
transferring the substrate from an ambient environment into a clean environment,
heating the substrate to at least a first temperature of between about one hundred
5 and fifty centigrade and about three hundred and fifty centigrade within
the clean environment,
maintaining the substrate at no less than the first temperature within the clean
environment,
selectively transferring the substrate within the clean environment to more than
10 one processing chambers, and processing the substrate in the more than
one processing chambers by,
performing an initial heating of the substrate in a degassing chamber,
etching the substrate in an etch chamber to form a via,
depositing a layer of titanium within the via in a first deposition chamber,
15 and
depositing a layer of titanium nitride over the layer of titanium in a second
deposition chamber, and
transferring the substrate from the clean environment into the ambient
environment.
2. (original) The method of claim 1 wherein the step of maintaining the substrate at
no less than the first temperature within the clean environment comprises heating
all of the clean environment to at least the first temperature.
3. (original) The method of claim 1 wherein the step of maintaining the substrate at
no less than the first temperature within the clean environment comprises
transferring and processing the substrate quickly through the more than one
processing chambers within the clean environment so that the substrate does not
5 have time to cool below the first temperature.

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4. (original) The method of claim 1 wherein the step of maintaining the substrate at no less than the first temperature within the clean environment comprises heating the substrate to at least the first temperature within each of the more than one processing chambers, and transferring the substrate quickly between the more than one processing chambers within the clean environment so that the substrate does not have time to cool below the first temperature between the more than one processing chambers.
- 5.
5. (cancelled)
6. (cancelled)
7. (original) The method of claim 1 further comprising the steps of reducing a pressure within the clean environment to a base pressure of between about 10^{-7} torr and about 10^{-9} torr.
8. (original) The method of claim 1 wherein the step of processing the substrate in the more than one processing chambers further comprises selectively adjusting a pressure within the more than one processing chambers while processing the substrate in the more than one processing chambers.
9. (cancelled)
10. (cancelled)
11. (cancelled)
12. (cancelled)
13. (cancelled)
14. (cancelled)
15. (cancelled)
16. (cancelled)
17. (cancelled)
18. (cancelled)
19. (cancelled)
20. (cancelled)